

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	28	("5963810") or ("6027976") or ("20020197790") or ("20030045080") or ("20020197790") or ("6514828") or ("6436777") or ("20030045080") or ("6544906") or ("6184072") or ("6420279") or ("20030032303") or ("5783478") or ("6625217") or ("6306742") or ("5891798")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/04 15:59
L3	6	2 and (high k gate dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/01/04 16:02
L4	1462619	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/01/04 16:02
L5	5	4 and ((high k gate dielectric) with substrate) and ((wet chemical treatment) with impurit\$4 with oxygen)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/01/04 16:19
L6	5	4 and (high k gate dielectric) and ((wet chemical treatment) with impurit\$4 with oxygen)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/01/04 16:20
L7	5	4 and (high k gate dielectric) and (wet chemical treatment) and impurit\$4 and oxygen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/01/04 16:21
L8	14	4 and (high k gate dielectric) and (wet chemical) and impurit\$4 and oxygen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/01/04 16:22